

**AMENDMENTS TO THE CLAIMS**

1. (Currently Amended) A method for manufacturing a white light source, the method including following steps:

providing a radiation source; and

providing a semiconductor-type phosphor with (Zn, Cd)S:M,N being a host matrix with foreign ions added thereto as luminescence centers, wherein M is one of Ag ion, Cu ion and Cl ion or a combination thereof, and N is one of Ag ion, Cu ion and Cl ion or a combination thereof;

wherein the radiation source emits light ranging from about 495nm (blue-green light) to 340nm (ultra-violet).

2. (Cancelled)

3. (Original) The method for manufacturing a white light source as in claim 1, wherein the radiation source is a light emitting diode.

4. (Currently Amended) The method for manufacturing a white light source as in claim 1, wherein the radiation source comprises an electron beam ~~and~~or plasma.

5. (Original) The method for manufacturing a white light source as in claim 1, wherein the semiconductor-type phosphor is prepared by chemosynthesis, solid-gas sintering, direct reaction or organic metal thermal decomposition.

6. (Currently Amended) The method for manufacturing a white light source as in claim 1, wherein the semiconductor-type phosphor is adjusted in weight ratio with respect to a ~~packing~~ material mixed with the phosphor.

7. (New) The method for manufacturing a white light source as in claim 1, wherein the semiconductor-type phosphor is implemented as  $(\text{Zn,Cd})\text{S}:\text{Ag}^+, \text{Cl}^-$ .